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► **To cite this version:**

Jean-Pierre Landesman, Daniel T Cassidy, Marc Fouchier, Erwine Pargon, Christophe Levallois, et al.. Mechanical Stress in InP Structures Etched in an Inductively Coupled Plasma Reactor with Ar/Cl-2/CH4 Plasma Chemistry. *Journal of Electronic Materials*, 2018, Special Section: 17th Conference on Defects-Recognition, Imaging and Physics in Semiconductors (DRIP XVII), 47 (9), pp.4964-4969. 10.1007/s11664-018-6152-6 . hal-01861357

**HAL Id: hal-01861357**

**<https://univ-rennes.hal.science/hal-01861357v1>**

Submitted on 10 Sep 2018

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# Mechanical Stress in InP Structures Etched in an Inductively Coupled Plasma Reactor with Ar/Cl<sub>2</sub>/CH<sub>4</sub> Plasma Chemistry

JEAN-PIERRE LANDESMAN<sup>1,2</sup>, DANIEL T. CASSIDY<sup>2</sup>, MARC FOUCHIER<sup>3</sup>, ERWINE PARGON<sup>3</sup>, CHRISTOPHE LEVALLOIS<sup>4</sup>, MERWAN MOKHTARI<sup>1</sup>, JUAN JIMENEZ<sup>5</sup>, and ALFREDO TORRES<sup>5</sup>

1.- Univ Rennes, CNRS, IPR - UMR 6251, F-35000 Rennes, France. 2.- McMaster University, Department of Engineering Physics, 1280 Main Street West, Hamilton, Ontario, L8S 4L7, Canada. 3.- Univ Grenoble Alpes, CNRS, LTM, F-38000 Grenoble, France. 4.- Univ Rennes, INSA Rennes, CNRS, Institut FOTON - UMR 6082, F-35000 Rennes, France. 5.- GdS Optronlab, Dpto. Fisica de la Materia Condensada, Universidad de Valladolid, 47011 Valladolid, Spain.

Corresponding author: JEAN-PIERRE LANDESMAN. e-mail : [Jean-Pierre.Landesman@univ-rennes1.fr](mailto:Jean-Pierre.Landesman@univ-rennes1.fr) – Telephone: +33 2 23 23 38 51

## Abstract

We investigate the crystal lattice deformation that can occur during the etching of structures in bulk InP using SiN<sub>x</sub> hard masks with Ar/Cl<sub>2</sub>/CH<sub>4</sub> chemistries in an inductively coupled plasma (ICP) reactor. Two techniques were used: degree of polarization (DOP) of the photo-luminescence (PL), which gives information on the state of mechanical stress present in the structures, and spectrally resolved cathodo-luminescence (CL) mapping. This second technique also provides elements on the mechanical stress in the samples through analysis of the spectral shift of the CL intrinsic emission lines. Preliminary DOP mapping experiments have been conducted on the SiN<sub>x</sub> hard mask patterns without etching the underlying InP. This preliminary study demonstrated the potential of DOP to map mechanical stress quantitatively in the structures. In a second step, InP patterns with various widths between 1 and 20 μm, and various depths between 1 and 6 μm, were analyzed by the 2 techniques. DOP measurements were made both on the (100) top surface of the samples and on the (110) cleaved cross section. CL measurements were made only from the (100) surface. We observed that inside the etched features, close to the vertical etched walls, there is always some compressive deformation, while it is tensile just outside the etched features. The magnitude of these effects depends on the lateral and depth dimensions of the etched structures, and on the separation between them (the tensile deformation increases between them due to some kind of proximity effect when separation decreases).

**Key words:** indium phosphide, photonic devices, plasma etching, mechanical stress

## INTRODUCTION

Plasma etching is broadly used nowadays in nanotechnology platforms, both in research, development and production, for the fabrication of a large number of components and integrated circuits. A good example of a family of such components is the photonic devices that can be fabricated on InP. One major drawback of plasma etching is the creation of structural and chemical damage in the vicinity of the etched surfaces. The defects introduced change the electro-optical properties of the semiconductor, thus ultimately compromising the device performance. Different studies have already reported on the damage created on flat surfaces exposed to reactive plasmas [1-3], either by identifying the structural and chemical defects, or by analyzing the changes in material electronic and optical properties due to damage. The degree of damage depends on the plasma etching parameters and notably it has been demonstrated that ion bombardment is mainly responsible for defect generation. Phenomena such as ion channeling combined with diffusion can create defects as deep as hundreds nm below the etched surface [4-7]. In GaAs etched with SiCl<sub>4</sub> under a self-bias voltage of 80 V damage was found at depths of the order of 150 nm below the etched surface [7]. In a recent study, we have examined the impact of exposing InP materials, with InAsP quantum wells (QWs), to different etching plasmas based on chlorine, in inductively coupled plasma (ICP) reactors. We observed modifications of the QWs PL at depths up to 1 μm, even if the self-bias voltage is limited to less than 100 V [8]. Only a few studies have been dedicated to the plasma induced damage at the pattern sidewalls where the etching mechanisms are radically different from what happens on bottom surfaces. Indeed, the pattern sidewalls are subjected to a low ion flux at grazing incidence compared to flat surfaces that are exposed to a high ion flux at normal incidence. Moreover, sidewalls are often protected by passivation layers during the etching. This could play a role in the reduction of damage at the sidewalls by limiting radical diffusion or ion penetration [9]. There is clearly today a lack of knowledge on by which mechanisms and to what extent the plasma etching process induces damage at the III-V pattern sidewalls and the consequence it has on the device performance and the whole system functionality.

We propose in this work to get some preliminary insights on the impact of plasma patterning on optical modifications of InP features. We focus on the lattice deformation that can occur during the etching of structures in bulk InP using chlorine chemistries in an ICP reactor. This deformation is measured and mapped using two complementary experimental techniques, degree of polarization (DOP) of the photo-luminescence (PL) and cathodo-luminescence (CL). Both techniques have already been used to map crystal deformations resulting from the presence of mechanical stresses in devices [10-12]. DOP is sensitive to non-biaxial deformations perpendicular to excitation beam propagation direction, whereas CL is sensitive mainly to the hydrostatic part of the deformation tensor, through the spectral shift of the emission band. Furthermore, both techniques have mapping capabilities, albeit different spatial resolution. Thus, if some local deformation results from the plasma processing of dedicated test features, the combination of the two techniques should first give us confidence in the identification of this deformation, and second provide a way to estimate quantitatively the different elements of the strain tensor.

## EXPERIMENTAL

The samples for this study are etched in bulk InP (100) wafers (n-type, S-doped,  $n=1.8 \times 10^{18} \text{ cm}^{-3}$ ) on which a 500 nm thick SiN<sub>x</sub> hard mask layer is realized by plasma enhanced chemical vapor deposition. The etched features are

76 rectangular-shaped lines, having lateral dimension  $L = 0.5, 1, 6, 10$  and  $20 \mu\text{m}$ , and aligned along the (110) direction of  
 177 InP. These lines can be isolated, or grouped in series where the spacing between lines is  $S = 0.5, 1, 2, 3, 6$  or  $10 \mu\text{m}$ .  
 278 After resist deposition, e-beam lithography, opening of this mask layer forming stripes (using a  $\text{CF}_4/\text{CH}_2\text{F}_2/\text{Ar}$  plasma)  
 379 and stripping of resist (using an  $\text{O}_2$  plasma), the  $\text{SiN}_x$  patterns are transferred into the InP substrate. This is done with a  
 480  $\text{CH}_4/\text{Cl}_2/\text{Ar}$  plasma operated in an ICP reactor equipped with a hot cathode. During this step the samples are heated to a  
 581 temperature of  $200^\circ\text{C}$ . The etch rate under the conditions of this study is approximately  $900 \text{ nm/min}$ . After etching, the  
 682  $\text{SiN}_x$  hard mask and the passivation layers formed on the InP sidewalls are removed by a dual step cleaning procedure  
 783 using  $\text{O}_2$  plasma followed by 49% HF dip.

884 DOP characterization was performed using  $633 \text{ nm}$  laser excitation, at room temperature. Details on this technique can  
 985 be found in [10] and [11]. We just recall here that the DOP signal measured along direction “y” can be written as

$$\text{DOP}_y = \frac{L_x - L_z}{L_x + L_z} = -C_\varepsilon(\varepsilon_{xx} - \varepsilon_{zz}), \quad (1)$$

1287 where x and z denote the 2 directions perpendicular to y, and therefore belong to the plane of the surface being  
 1388 measured.  $L_x$  and  $L_z$  are the components of the spectrally-integrated PL with polarization along these 2 directions.  $\varepsilon_{xx}$   
 1489 and  $\varepsilon_{zz}$  are the linear crystal deformations.  $C_\varepsilon$  is a calibration constant which has been determined experimentally for  
 1590 some InP surfaces [10]. Note that in all the figures discussed here x is the horizontal axis, z the vertical axis. As shown  
 1691 in [10], the sensitivity of the DOP technique is such that deformations of  $10^{-5}$  can be detected. In addition to the term  
 1792  $\text{DOP}_y$ , the measurements also yield the rotated DOP (ROP) defined by

$$\text{ROP}_y = \frac{L_{x'} - L_{z'}}{L_{x'} + L_{z'}} = 2C_\varepsilon\varepsilon_{xz}, \quad (2)$$

2094 where  $x'$  and  $z'$  are rotated by  $45^\circ$  with respect to x and z.  $2\varepsilon_{xz}$  is the angular deformation in the plane.

2195 As an example, fig. 1 shows the output of a DOP measurement on the top surface of a sample with the  $\text{SiN}_x$  mask stripes  
 2296 defined, just before the InP etching in the ICP reactor (isolated line with  $L=10 \mu\text{m}$ ).

2397 CL mapping was performed with a beam voltage of  $5 \text{ kV}$ , at room temperature. In the present study, we will only discuss  
 2498 the spectral shifts of the CL intrinsic band associated with band to band transitions. These shifts are related to the  
 2599 hydrostatic part of the crystal deformation, as the spectral resolution does not allow for the separation of different  
 2600 contributions which would result from non-equivalent deformations in the 3 directions [12]. Under this assumption, the  
 2701 CL peak shifts  $\Delta E_{\text{CL}}$  may be related to the hydrostatic part of the stress tensor through the formula:

$$\Delta E_{\text{CL}} = k.(\sigma_{xx} + \sigma_{yy} + \sigma_{zz}), \quad (3)$$

2802 where the constant k has been calculated to be  $-11.10^{-8} \text{ meV/Pa}$  in the case of InP [13]. Note that a positive energy shift  
 3003 is associated to a compressive stress.

3104 Fig. 2 shows two CL spectra, measured respectively on a raw wafer that will be used as a deformation-free reference and  
 3205 in the center of an etched line ( $L=1 \mu\text{m}$ ). For the determination of the spectral shifts, we use a simple procedure where  
 3306 the central part of the band is fitted by a Gaussian profile. This procedure yields an accuracy of around  $1 \text{ meV}$  for the  
 3407 determination of the spectral shifts.  
 3508

## 3609 RESULTS AND DISCUSSION

3710 When discussing mechanical stress, it is always useful to start from a reference for which the stress profile is known. In  
 3811 our case, the reference state consists of the sample with the  $\text{SiN}_x$  hard mask that has been opened to define the features to  
 3912 be etched, without having been transferred into the InP substrate. The situation in terms of the mechanical stress in such  
 4013 samples has been amply described in the literature [14, 15]. The distribution of the mechanical stress induced by  
 4114 dielectric stripes at semiconductor surfaces has also been measured, essentially by micro-Raman spectroscopy [16].

4215 On fig. 1 we can see that the DOP is positive inside the stripe, with a pronounced maximum value of around 2 % close to  
 4316 the edges. The ROP is uniform and negligible (within the limit of the instrument resolution). The total PL yield shows a  
 4417 minimum below the stripe. To better view the DOP variation, we averaged the DOP map in the vertical direction,  
 4518 assuming that there is no variation in this direction. The result is shown in fig. 3, where the DOP profiles for three  
 4619 isolated stripes are displayed ( $L=6, 10$  and  $20 \mu\text{m}$ ). The same trend is observed for the three stripes, however the positive  
 4720 edge peak is maximum for  $L=6 \mu\text{m}$ . The maximum DOP close to stripe edges is around 2 %, which corresponds to a  
 4821 differential linear deformation ( $\varepsilon_{xx} - \varepsilon_{zz}$ ) of approximately  $3 \times 10^{-4}$ .

4922 We also mapped the DOP on cleaved cross sections of the reference samples, below the stripes. Fig. 4 displays the DOP  
 5023 and ROP maps below two isolated stripes ( $L=10$  and  $20 \mu\text{m}$ ). These results clearly reveal the deformation field induced  
 5124 by the  $\text{SiN}_x$  stripes. The ROP maps show that some angular deformation is also present below the stripes.

5225 To complete the picture for the reference samples, we did analytical modelling of the surface DOP profiles of fig. 3  
 5326 using the concentrated edge force model (see e.g. [14]). More precisely, we assumed that at any point below the  $\text{SiN}_x$   
 5427 stripe, the stress tensor is mainly due to the film itself since there is a difference in thermal expansion coefficients  
 5528 between  $\text{SiN}_x$  and InP. A second contribution is related to the two film edges. For any point away from the stripe, we  
 5629 only take into account the contribution from the film edges. The finite probing depth of the PL was introduced  
 5730 empirically by defining a quantized probed depth below the surface (this was an adjustable parameter). Finally, in order  
 5831

133 to reproduce the finite DOP that was measured close to stripe centers, we also had to assume that the effect of the  
134 difference in thermal expansion coefficients is anisotropic in the plane of the film even for  $L=20\ \mu\text{m}$  (we could check  
135 experimentally that this is no more the case for much larger stripes). The results of this fitting procedure are illustrated  
136 on fig. 5. The agreement is acceptable, given the limited number of adjustable parameters. Note that the positive and  
137 negative peaks near the edges derive from the singularities in the concentrated edge force. Geometrical discontinuities  
138 always induce singularities in the mechanical stresses.

139 Next we measured surface DOP maps after etching the InP and subsequent removal of the  $\text{SiN}_x$  mask and edge walls  
140 passivation. Fig. 6 shows the vertical DOP averages for isolated etched ridges ( $L=6, 10$  and  $20\ \mu\text{m}$ ). Etch depth is  $3\ \mu\text{m}$ .  
141 The singularities near the edges are now more pronounced, but the curves retain the general shape of the DOP profiles  
142 on the reference sample. There is no more DOP inside the ridges. The DOP is very positive in the ridges close to edges,  
143 whereas it is negative in the etched areas close to the ridges. The magnitude of the DOP seems to be highest for  $L=20$   
144  $\mu\text{m}$ .

145 Since the general shape is similar to that on the reference sample, we found it interesting to fit the curves with the same  
146 concentrated edge force model. The results are shown in fig. 7. The agreement is still acceptable.

147 As for the cross section observations, the cleavage quality was unfortunately too poor to get useful DOP maps in the  
148 case of etched samples.

149 In the second part of our study, we measured CL profiles on the very same etched samples, from the top surface only.  
150 Displayed on fig. 8 are CL profiles across different series on the etched sample (etched depth  $3\ \mu\text{m}$ ), with  $L$  fixed at  $1$   
151  $\mu\text{m}$  and variable  $S$ . The spectral shift on fig. 8 was obtained by subtracting to the measured CL peak positions the value  
152 determined on a reference wafer identical to the etched wafer, having seen no processing at all. One can see that the  
153 hydrostatic equivalent deformation within the ridge for  $L=1\ \mu\text{m}$  does not seem to depend significantly on the spacing  $S$ .  
154 On the other hand, the amount of deformation in the spacings, in particular close to the ridges, seems to increase for  
155 decreasing  $S$  values. Positive peak shifts indicate a compressive equivalent deformation, whereas negative peak shifts  
156 indicates tensile deformation [13]. For spacings up to  $S=1\ \mu\text{m}$ , there is a close to ideal compensation between  
157 compressive deformation within the stripe and tensile deformation between stripes. For larger spacings, the tensile  
158 deformation near the ridge seems to relax as one goes away from the ridge. These observations are in overall agreement  
159 with the DOP measurements, although the details of the information derived from the two methods differ. In a first  
160 approximation, the CL curves have to be discussed in terms of the equivalent hydrostatic deformation while the DOP  
161 data are related to non-biaxial deformations in the plane of the measurement. DOP indicates compression in the ridges  
162 close to the edges, and tension outside (however due to the lower resolution in DOP we cannot resolve the profile for  
163 ridges with  $L<6\ \mu\text{m}$ ). Additional results on series with different spacings  $S$  (not shown here) also show that the DOP  
164 signal within the ridges with fixed  $L$  does not depend on the spacing  $S$ , while the DOP in the spacings increases for  
165 smaller spacings. This is what we call the “cumulative” effect of nearby ridges.

166 On fig. 9 one can see the complementary trend to that of fig. 8: when the spacing  $S=1\ \mu\text{m}$  is fixed, the amount of  
167 compressive deformation within the ridges is higher for narrower ridges. For broader ridges ( $L=6\ \mu\text{m}$ ) the deformation is  
168 relaxed near ridge center, a result totally in agreement with the DOP observation. Tensile deformation inside the  
169 spacings with  $S=1\ \mu\text{m}$  appears not very dependent of the ridge width, except for  $L=0.5\ \mu\text{m}$ .

170 Our observations with the two complementary techniques clearly show the presence of crystal deformation in and close  
171 to the etched features in InP. This might have a significant impact in the design and performances of photonic structures  
172 whose fabrication relies on etching of deep structures such as those investigated herein. Numerical fits with an analytical  
173 model based on the concentrated edge force model help getting an insight into the details of the deformation profiles.  
174 The next step will be the design of a model for the prediction of the deformation tensor at each point in the vicinity of  
175 the etched features, with some assumption about the physical origin of the mechanical deformation. Such a tool would  
176 be helpful for photonic circuit designers.

#### 177 Acknowledgments

178 A. Torres and J. Jiménez were funded by Junta de Castilla y León (Grants VA293U13 and VA081U16)

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FIGURE CAPTION

**Fig. 1:** Color scale maps of the DOP, ROP and PL yield for the reference sample (10  $\mu\text{m}$  wide  $\text{SiN}_x$  stripe at the (100) surface of InP). Measurements are along the normal to the (100) surface. Values for the DOP and ROP are indicated in % on the color scale to the right of each map. PL yield is given in counts (color scale to the right of the corresponding map).

**Fig. 2:** CL spectrum on a reference wafer (red dash line) and average of the spectra in etched stripes  $L=1 \mu\text{m}$  with different spacings (blue; etched depth  $3 \mu\text{m}$ ).

**Fig. 3:** DOP curves obtained from averaging the maps such as the one on fig. 1 along the length of the  $\text{SiN}_x$  stripes, for width  $20 \mu\text{m}$  (black),  $10 \mu\text{m}$  (red) and  $6 \mu\text{m}$  (dash blue).

**Fig. 4:** Color scale maps of the DOP and ROP for the reference sample, for measurements perpendicular to the cleaved cross section. DOP and ROP values are indicated in % on the color scale bars.  $20 \mu\text{m}$  stripe: DOP (a), ROP (b);  $10 \mu\text{m}$  stripe: DOP (c), ROP (d).

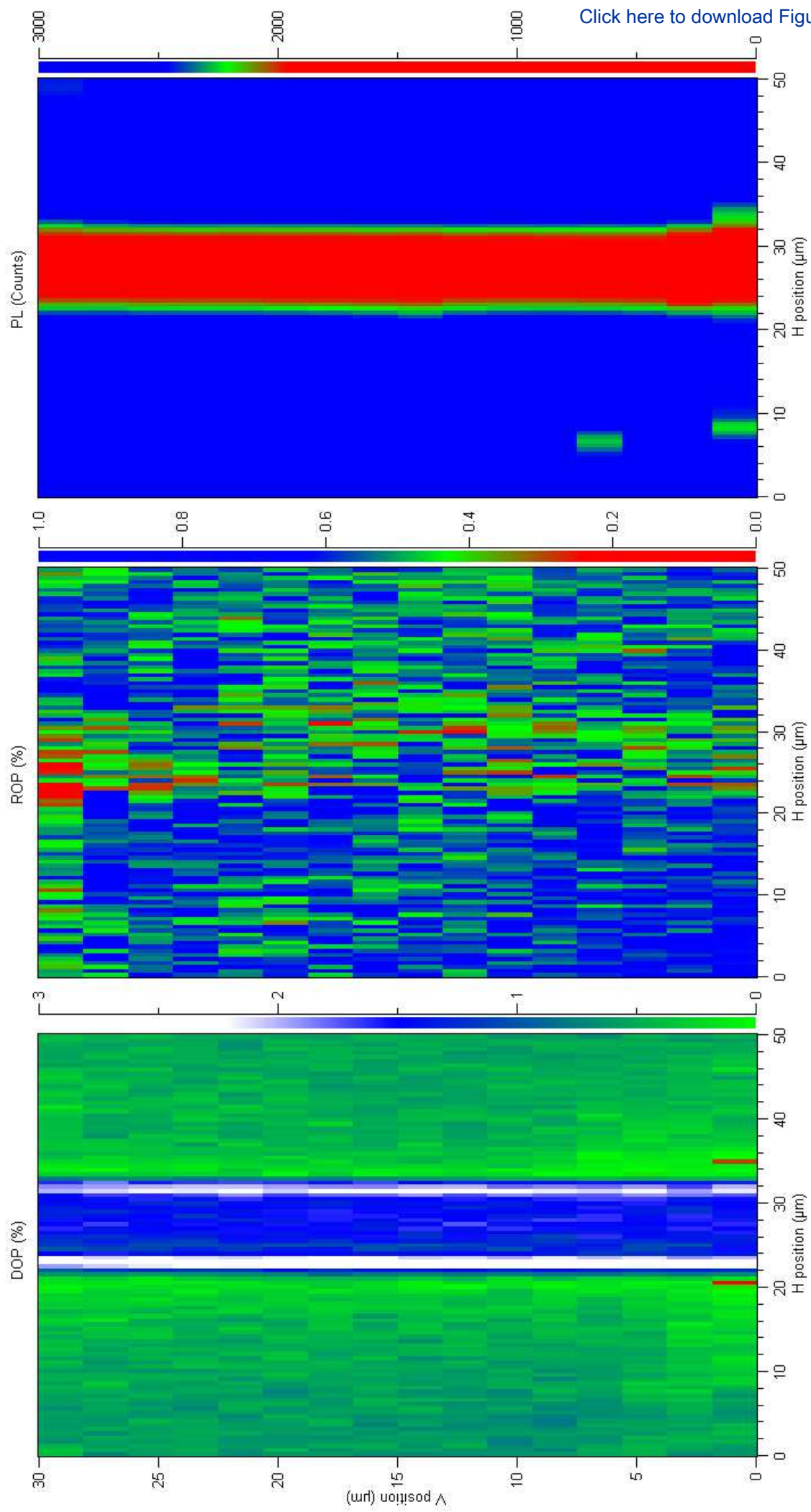
**Fig. 5:** Analytical fits with the edge force model to the DOP profiles for  $10 \mu\text{m}$  (a) and  $20 \mu\text{m}$  (b) stripes on the reference sample. Blue curves: experimental data; red dash curves: model.

**Fig. 6:** Average DOP curves on isolated ridges of the etched sample (etched depth  $3 \mu\text{m}$ ), for width  $20 \mu\text{m}$  (black),  $10 \mu\text{m}$  (red) and  $6 \mu\text{m}$  (dash blue).

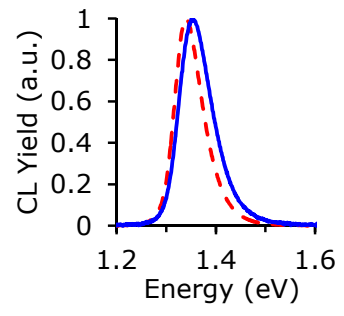
**Fig. 7:** Analytical fits with the edge force model to the DOP profiles for  $10 \mu\text{m}$  (a) and  $20 \mu\text{m}$  (b) isolated ridges on the etched sample (etch depth  $3 \mu\text{m}$ ). Blue curves: experimental data; red dash curves: model.

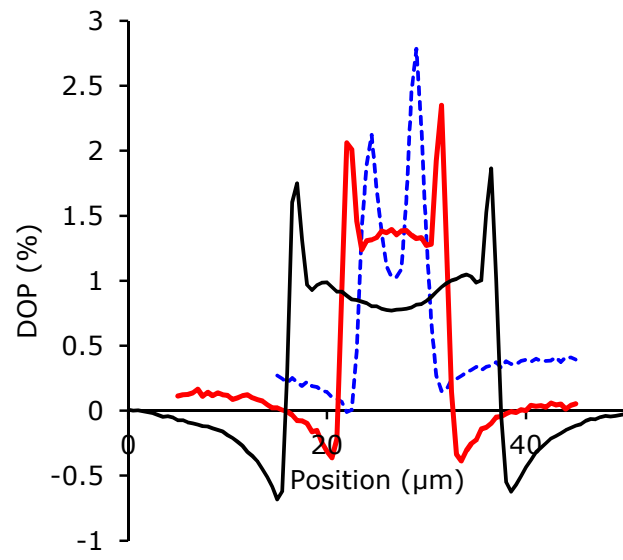
**Fig. 8:** CL spectral shift (difference between peak position measured on the etched sample and on a reference wafer) from the surface of the etched sample (etched depth  $3 \mu\text{m}$ ) for series with line width  $L=1 \mu\text{m}$  and different spacings  $S$ . Black  $\blacksquare$ :  $S=0.5 \mu\text{m}$ ; Red  $\blacktriangle$ :  $S=1 \mu\text{m}$ ; Green  $\blacklozenge$ :  $S=2 \mu\text{m}$ ; Blue X:  $S=3 \mu\text{m}$ ; Pink +:  $S=6 \mu\text{m}$ ; Grey  $\star$ :  $S=12 \mu\text{m}$ ; Light blue curve: isolated line  $L=1 \mu\text{m}$ .

**Fig. 9:** CL spectral shift measured from the surface of the etched sample (etched depth  $3 \mu\text{m}$ ) for series with different line widths  $L$  and spacing  $S = 1 \mu\text{m}$ . Blue  $\blacklozenge$ :  $L=6 \mu\text{m}$ ; Red  $\blacksquare$ :  $L=1 \mu\text{m}$ ; Black  $\blacktriangle$ :  $L=0.5 \mu\text{m}$ .









Figure

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